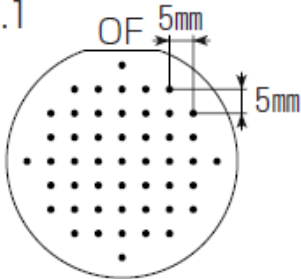


InP Single Crystal Wafers(Semi-Insulating Type)

Standard Specifications

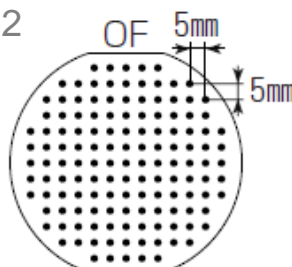
Growth Method·Dopant	VB(*1)·Fe			
Fe Concentration(wtppm)	≥ 0.3			
Resistivity($\Omega \cdot \text{cm}$)	$\geq 1 \times 10^7$			
Mobility($\text{cm}^2/\text{V} \cdot \text{sec}$)	$\geq 2 \times 10^3$			
EPD Average(cm^{-2})	$\leq 5 \times 10^3$		$\leq 10 \times 10^3$	
Measuring Points of EPD	Fig.1	Fig.2	Fig.3	Fig.4
Diameter(mm)	50.0 \pm 0.3	76.0 \pm 0.3	100.0 \pm 0.3	150.0 \pm 0.3
OF(mm)(Fig. 5)(*2)	16.0 \pm 1.0	22.0 \pm 1.0	32.5 \pm 1.0	—
IF(mm)(Fig. 5)	7.0 \pm 1.0	12.0 \pm 1.0	18.0 \pm 1.0	—
Notch	—	—	—	SEMI standard
Edge Rounding(mmR)	0.25(Conform to SEMI Standards)			
Thickness(μm)	350 \pm 15	600 \pm 15	625 \pm 25	675 \pm 25
Orientation	$(100) \pm 0.3^\circ$			
Surface Finish	P/LE, P/P		P/P	
Surface Clean(*3)	EW			
Flatness·LPD(*4)	Refer to other specification			
Package	Individual Container			

Fig.1



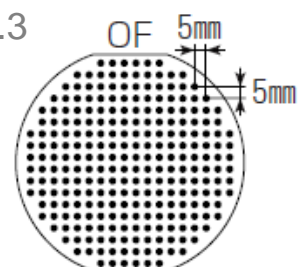
49 Points

Fig.2



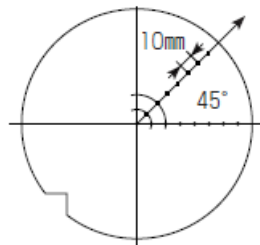
137 Points

Fig.3



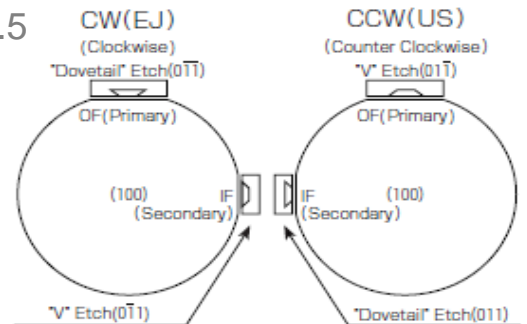
256 Points

Fig.4



Notch 15 Points

Fig.5



Notes

- (*1) VB : Vertical Boat
- (*2) High Precision OF($\pm 0.02^\circ$) is available.
- (*3) EW : Etched Wafer
- (*4) LPD : Light Point Defects

Attached Data

- Standard : Resistivity, Mobility, Diameter, OF, IF, Thickness(min.~max.), EPD Map
- Option : Accuracy of Orientation, Flatness, Light Point Defects